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filed July 6, 1995. The entire disclosures of the above applications are hereby incorporated by reference. --

IN THE CLAIMS:

Please cancel all of the claims, i.e., claims 1-16, without prejudice and substitute therefore the following new claims 17-50:

-- 17. A material comprising an organic die-bonding film having a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher when a semiconductor has been bonded to a support material under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm^2.

18. A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm^2, and having a saturation moisture absorption of 1.0% by volume or less.

19. A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm^2, and having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

20. A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C

temperature and pressure of 0.1-30 gf/mm^2, having a void volume of 10% or less in terms of voids present in the material and at an interface between said material and a support member at a stage where a semiconductor has been bonded to a support member by said material.

21. A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm^2, having a residual volatile component in an amount of not more than 3.0% by weight.

22. A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm^2, having a water absorption of 1.5% by volume or less.

23. A material according to claim 17, comprising an organic die-bonding film further having a modulus of elasticity of 10 Mpa or less at a temperature of 250°C.

24. A material according to claim 23, comprising an organic die-bonding film further having a water absorption of 1.5% by volume or less.

25. A material according to claim 24, comprising an organic die-bonding film further having a residual volatile component in an amount of not more than 3.0% by weight.

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26. A material according to claim 25, comprising an organic die-bonding film further having a saturation moisture absorption of 1.0% by volume or less.

27. A material according to claim 26, comprising an organic die-bonding film further having a void volume of 10% or less in terms of voids present in the material and at an interface between said material and a support member at a stage where a semiconductor had been bonded to a support member by said material.

28. A material according to claim 20, comprising an organic die-bonding film further having a water absorption of 1.5% by volume or less, having a saturation moisture absorption of 1.0% by volume or less, and having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

29. A material according to claim 20, comprising an organic die-bonding film further having a saturation moisture absorption of 1.0% by volume or less, having a modulus of elasticity of 10 MPa or less at a temperature of 250°C, and having a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher.

30. A material comprising an organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm^2, and having a water absorption of 1.5% by volume or less, a saturation moisture absorption of 1.0% by volume or less, a modulus of elasticity of 10 MPa or less at a temperature of 250°C, a void volume of 10% or less in terms of voids present in the material and at an interface between said material and a support member at a stage where a semiconductor has been bonded to a support member by said material, a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher at a stage where a semiconductor has been bonded to a support member with said material, and a residual volatile component in an amount of not more than 3.0% by weight.

31. A material according to claim 17, being a self-supporting film.

32. A material according to claim 30, being a self-supporting film.

33. A material according to claim 17, having a single layer structure.

34. A material according to claim 30, having a single layer structure.

35. A material according to claim 17, wherein said material is an organic material comprising one or more components selected from the group consisting of epoxy resin, silicone resin, acrylic resin, and polyimide resin.

36. A material according to claim 30, wherein said material is an organic material comprising one or more components selected from the group consisting of epoxy resin, silicone resin, acrylic resin, and polyimide resin.

37. A material according to claim 17, wherein said material is an organic material comprising a polyimide resin.

38. A material according to claim 30, wherein said material is an organic material comprising a polyimide resin.

39. A material according to claim 17, wherein said material is an organic material comprising a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-dimethylphenyl)methane.

40. A material according to claim 17, wherein said material is an organic material comprising a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 4,4'-diaminophenyl ether.

41. A material according to claim 17, wherein said material is an organic material comprising a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-diisopropylphenyl)methane.

42. A material according to claim 17, wherein said material is an organic material comprising a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

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43. A material according to claim 17, wherein said material is an organic material comprising a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride), 1,10-(decamethylene)bis(trimellitate anhydride, and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

44. A material according to claim 17, wherein said material is an organic material comprising a polyimide synthesized from 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

45. A material according to claim 17, wherein said material is an organic material comprising an epoxy resin.

46. A material according to claim 17, wherein said material is an organic material comprising a polyimide resin and an epoxy resin.

47. A material according to claim 35, further comprising a metal filler.

48. A material according to claim 36, further comprising a metal filler.